UMW IRLL014NTR

55V N-Channel MOSFET

1.Description

The SOT-223 package is designed for surface mountusing vapor phase , infra red , or wave soldering techniquests unique package design allows for easy automatic pickand-place as with other packages but hasthe added advantage of improved thermal performancedue to an enlarged tab for heatsinking . Power dissipationof 1 . OW is possible in a typical surface mount application

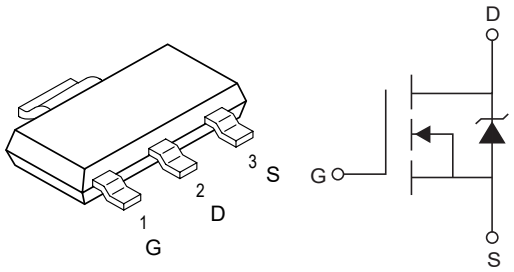
2.Features

- $V_{DS\ (V)}$=55V
- I_D=2A(V_{GS}=10V)
- $R_{DS(ON)}$<140mΩ(V_{GS}=10V)
- Surface Mount
- Advanced Process Technology
- Ultra Low On-resistance
- Dynamic dv / dt Rating
- Fast Switching

3.Pinning information

Pin	Symbol	Description
1	G	GATE
2	D	DRAIN
3	S	SOURCE

SOT-223 top view



4.Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	Rating	Units
Continuous Drain Current, V_{GS} @ 10V**	T_A=25°C	I_D	2.8	A
Continuous Drain Current, V_{GS}10V*	T_A=25°C		2	A
Continuous Drain Current, V_{GS}10V*	T_A=70°C		1.6	A
Pulsed Drain Current ①		I_{DM}	16	A
Power Dissipation(PcB Mount)**	T_A=25°C	P_D	2.1	W
Power Dissipation(PCB Mount)*	T_A=25°C		1	W
Linear Derating Factor (PCB Mount)*			8.3	mW°C
Gate-to-Source Voltage		V_{GS}	±16	V
Single Pulse Avalanche Energy②		E_{AS}	32	mJ

Avalanche Current①	I_{AR}	2	A
Repetitive Avalanche Energy①*	E_{AR}	0.1	mJ
Peak Diode Recovery dv/dt ③	dv/dt	7.2	V/ns
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	°C

5.Thermal resistance rating

Parameter	Symbol	Typ	Max	Units
Junction-to-Amb. (PCB Mount, Steady State)*	$R_{\theta JA}$	90	120	°C/W
Junction-to-Amb. (PCB Mount, Steady State)**	$R_{\theta JA}$	50	60	°C/W

6.Electrical Characteristics T_J=25°C

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=250μA, V_{GS}=0V	55			V
Breakdown Voltage Temp. Coefficient	$\Delta V_{(BR)DSS}/\Delta T_J$	Reference to 25°C,I_D=1mA		0.015		V/°C
Static Drain-to-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=2A ④			140	mΩ
		V_{GS}=5V, I_D=1.2A ④			200	mΩ
		V_{GS}=4V, I_D=1A ④			280	mΩ
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250μA	1		2	V
Forward Transconductance	g_{FS}	V_{DS}=25V, I_D=1A	2.3			S
Drain-to-Source Leakage Current	I_{DSS}	V_{DS}=55V, V_{GS}=0V			25	μA
		V_{DS}=44V, V_{GS}=0V, T_J=150°C			250	μA
Gate-to-Source Forward Leakage	I_{GSS}	V_{GS}=16V			100	nA
Gate-to-Source Reverse Leakage		V_{GS}=-16V			-100	nA
Total Gate Charge	Q_g	I_D=2A,V_{DS}=44V,V_{GS}=10V See Fig. 6 and 11 ④		9.5	14	nC
Gate-to-Source Charge	Q_{gs}			1.1	1.7	nC
Gate-to-Drain ("Miller") Charge	Q_{gd}			3	4.4	nC
Tum-On Delay Time	$t_{D(on)}$	V_{DD}=28V, I_D=2A, R_G=6Ω R_D=14Ω, See Fig. 12 ④		5.1		ns
Rise Time	t_r			4.9		ns
Turn-Off Delay Time	$t_{D(off)}$			14		ns
Fall Time	t_f			2.9		ns
Input Capacitance	C_{iss}	V_{GS}=0V, V_{DS}=25V, f=1MHz See Fig. 5		230		pF
Output Capacitance	C_{oss}			66		pF
Reverse Transfer Capacitance	I_s			30		pF

Continuous Source Current (Body Diode)	C_{rss}	MOSFET symbol showing the integral reverse p-n junction diode.			1.3	A
Pulsed Source Current (Body Diode)①	I_{SM}				16	
Diode Forward Voltage	V_{SD}	T_J=25°C,I_S=2A,V_{GS}=0V ④			1	V
Reverse Recovery Time	t_{rr}	T_J=25°C, I_F=2A		41	61	ns
Reverse Recovery Charge	Q_{rr}	dI/dt=100A/μs ④		73	110	nC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Notes:

① Repetitive rating; pulse width limited by max. junction temperature.(See fig.9)

② V_{DD}= 25V, starting T_J= 25°C,L= 4.0mH, R_G= 25Ω, I_{AS}= 4.0A.(See Figure 13)

③ I_{SD}≤ 2.0A, di/dt ≤ 170A/μs, V_{DD}≤ $V_{(BR)DSS}$, T_J≤ 150°C

④ Pulse width ≤ 300μs; duty cycle ≤ 2%.

7.1Typical Characterisitics

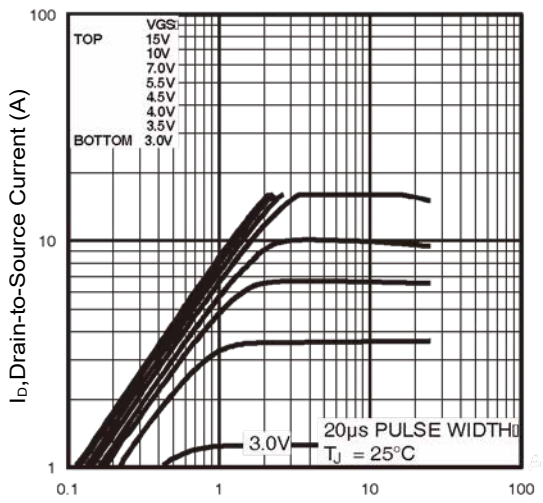


Figure 1: Typical Output Characteristics

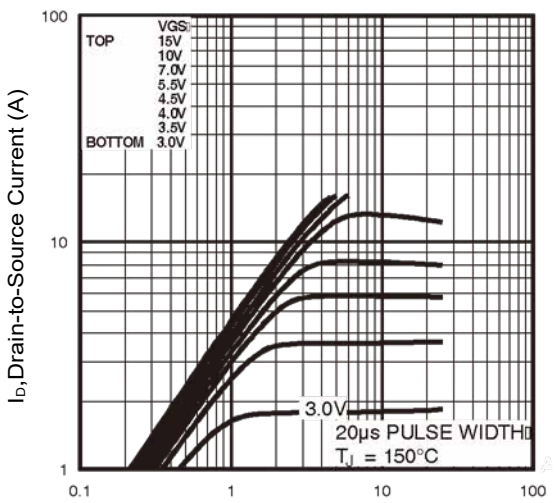


Figure 2: Typical Output Characteristics

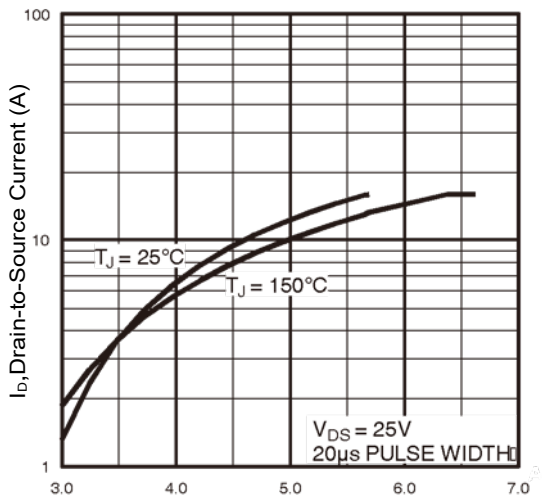


Figure 3: Typical Transfer Characteristics

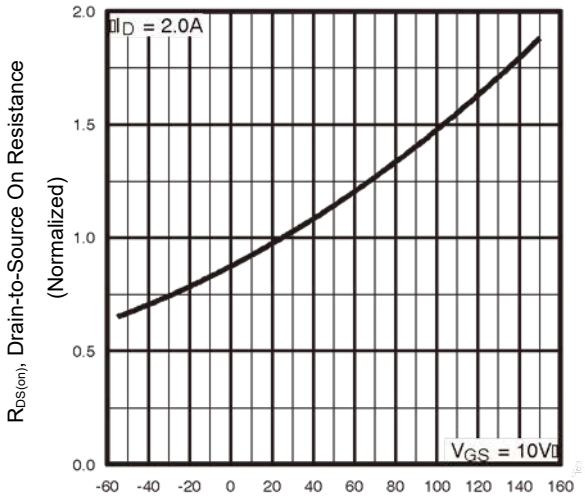
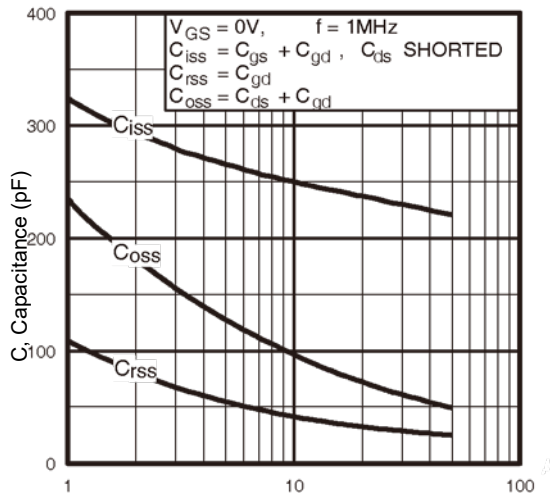


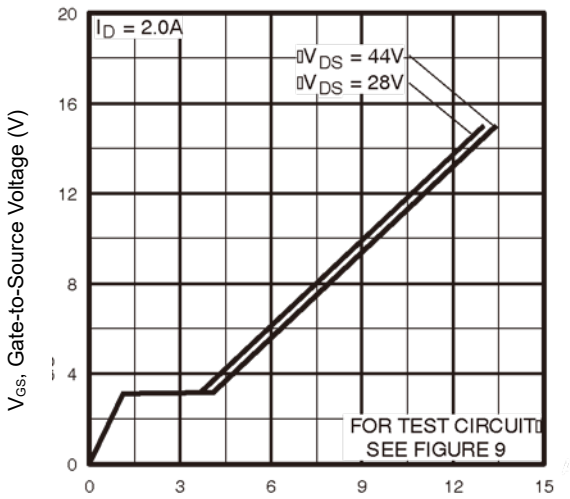
Figure 4: Nomalized On-ResistanceVs. Temperature

7.2Typical Characterisitics



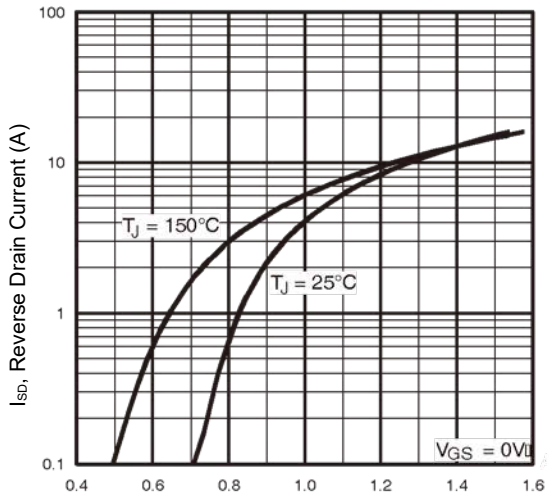
V_{DS} ,Drain-to-Source Voltage (V)

Figure 5: Typical Capacitance Vs. Drain-to-Source Voltage



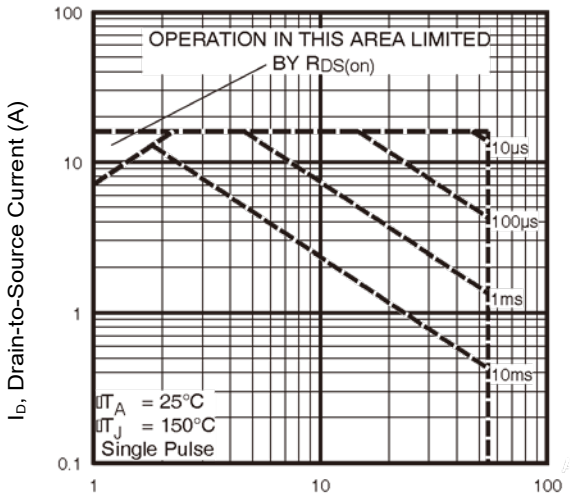
Q_G, Total Gate Charge (nC)

Figure 6: Typical Gate Charge Vs. Gate-to-Source Voltage



V_{SD}, Source-to-Drain Voltage (V)

Figure 7: Typical Source-Drain Diode Forward Voltage



V_{DS}, Drain-to-Source Voltage (V)

Figure 8: Maximum Safe Operating Area

7.3Typical Characterisitics

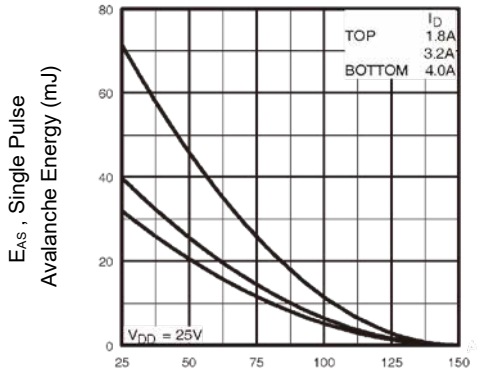


Figure 9: Maximum Avalanche Energy Vs. Drain Current

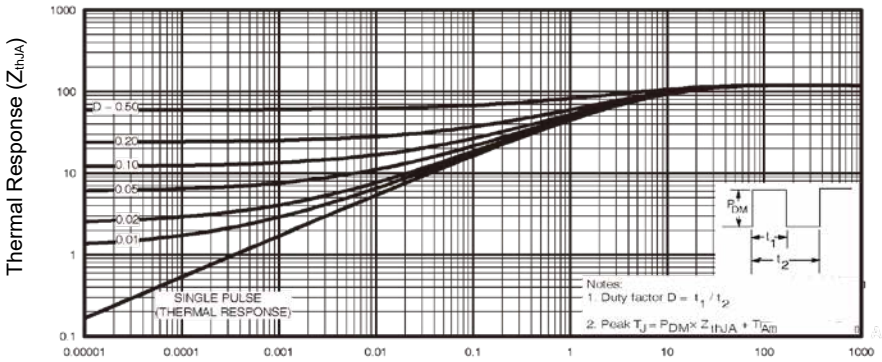


Figure 10: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

7.4Typical Characterisitics

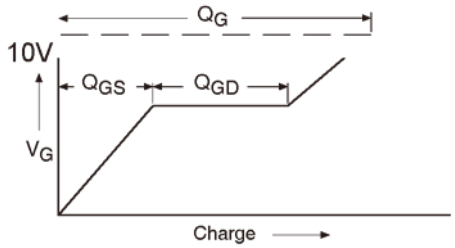


Figure 11a: Basic Gate Charge waveform

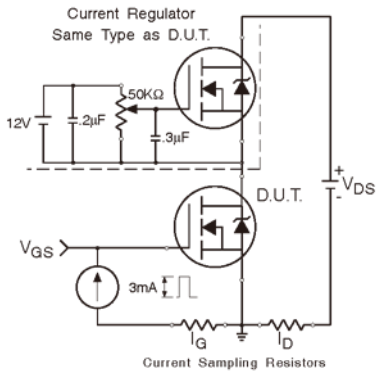


Figure 11b: Switching Time Test Circuit

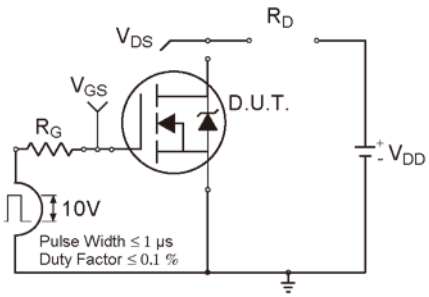


Figure 12a: Gate Charge Test Circuit

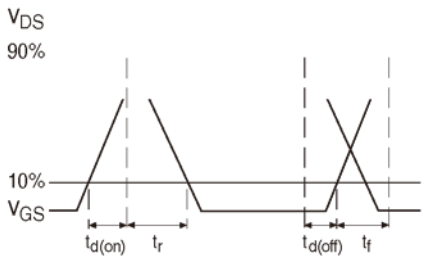


Figure 12b: Switching Time waveforms

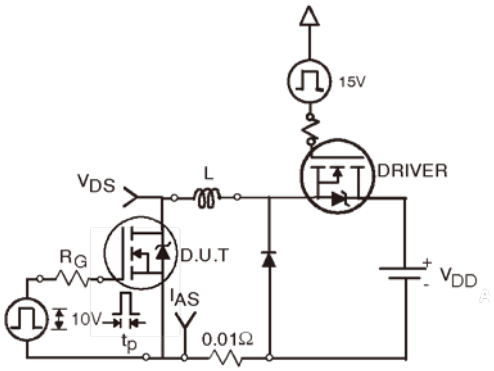


Figure 13a: Unclamped Inductive Test Circuit

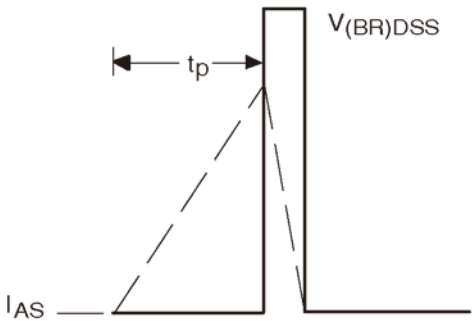
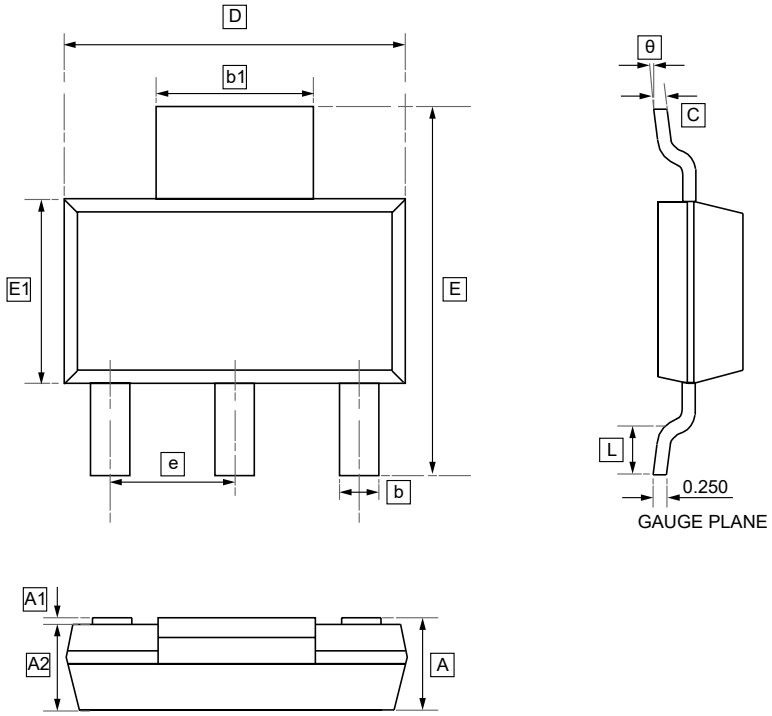


Figure 13b: Unclamped Inductive waveforms

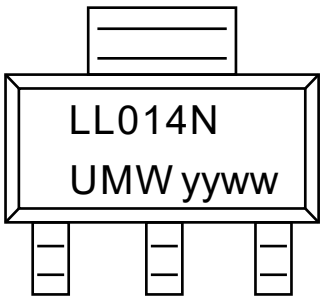
8.SOT-223 Package Outline Dimensions



DIMENSIONS (mm are the original dimensions)

Symbol	A	A1	A2	b	b1	c	D	E	E1	e	L	θ
Min	-	0.020	1.500	0.660	2.900	0.230	6.300	6.700	3.300	2.300	0.750	0°
Max	1.800	0.100	1.700	0.840	3.100	0.350	6.700	7.300	3.700	BSC	-	10°

9.Ordering information



yy: Year Code
ww: Week Code

Order Code	Package	Base QTY	Delivery Mode
UMW IRLL014NTR	SOT-223	2500	Tape and reel

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